

What is claimed is:

1. A flat panel display, comprising:
 - a glass substrate having an upper surface, which is divided into a displaying area and a surrounding frame area, said displaying area further comprising a plurality of pixel devices, each of said pixel devices comprising a thin film transistor (TFT) utilized as a switch;
 - a plurality of first conductive lines formed atop said frame area for controlling a portion of said TFTs;
 - a dielectric layer formed atop said frame area for covering said first conductive lines; and
 - a plurality of second conductive lines formed atop said dielectric layer for controlling the other said TFTs.
2. The flat panel display of claim 1, wherein said first conductive lines and said gate electrodes of said TFTs are formed in a metal layer.
3. The flat panel display of claim 1, wherein said second conductive lines and source/drain electrodes of said TFTs are formed in a metal layer.
4. The flat panel display of claim 1, wherein said first conductive lines are positioned along a boundary of the displaying area with a predetermined interval.
5. The flat panel display of claim 1, wherein said second conductive lines are positioned along a boundary of the displaying area with a predetermined interval.
6. The flat panel display of claim 1, wherein said dielectric layer is formed of silicon nitride.
7. A method of forming a flat panel display having a plurality of TFTs to control illumination of pixels, comprising the steps of:
 - forming a plurality of gate lines and a plurality of first conductive lines on a glass substrate, said first conductive lines connecting to part of said gate lines;
 - forming a dielectric layer on said glass substrate to cover said gate lines and said first conductive lines; and
 - forming a plurality of sources, drains, and second conductive lines on

said dielectric layer, and having said second conductive lines connect to rest of said gate lines.

8. The fabrication method of claim 7, wherein said step of forming said gate lines and said first conductive lines further comprises the steps of:

5 forming a first metal layer over the glass substrate; and

etching said first metal layer to form said gate lines and said first conductive lines, in which said first conductive lines connect part of said gate lines.

9. The fabrication method of claim 7, wherein said step of forming said 10 second conductive lines further comprises the steps of:

forming a second metal layer over said dielectric layer;

etching said second metal layer to form said sources, said drains, and said second conductive lines;

forming a passivation layer to cover said sources, said drains, and

15 said second conductive lines;

etching said passivation layer to form a plurality of openings to expose said second conductive lines and rest of said gate lines; and

forming a plurality of connecting structures on said passivation layer for filling said openings to connect said second conductive lines and rest

20 of said gate lines.

10. The fabrication method of claim 7, wherein an upper surface of said glass substrate includes a displaying area having said gate lines formed thereon and a surrounding frame area having said first conductive lines and said second conductive lines formed thereon.

25 11. The fabrication method of claim 7, wherein said first conductive lines are positioned along a boundary of said displaying area with a predetermined interval.

12. The fabrication method of claim 7, wherein said second conductive lines are positioned along a boundary of said displaying area with a 30 predetermined inter-line interval.

13. The fabrication method of claim 7, wherein said dielectric layer is formed of silicon nitride.

14. A liquid crystal display, which is comprised of a color filter layer, a liquid crystal layer, a TFT panel, and a backlight module, the TFT panel comprising:
- a rectangular glass substrate having an upper surface, which is divided into a rectangular displaying area positioned at a center of said upper surface and a surrounding frame area, a plurality of pixel devices formed on said display area, each of said pixel devices comprising a thin film transistor (TFT) utilized as a switch;
- a plurality of first conductive lines, formed atop said frame area and positioned along a side of said rectangular display area with a predetermined interval, utilized for controlling part of said TFTs, said first conductive lines and gate electrodes of said TFTs formed in a metal layer;
- a dielectric layer formed atop said frame area outside said side of said rectangular display area and covering said first conductive lines; and
- a plurality of second conductive lines, which is formed atop said dielectric layer and positioned along said side of said rectangular display region with a predetermined interval for controlling rest of said TFTs, said second conductive lines and source/drain electrodes of said TFTs being formed in a metal layer.
15. The liquid crystal display of claim 14, further comprises a driving circuit having connection with gates of said TFTs through said first conductive lines and said second conductive lines.
16. The liquid crystal display of claim 14, wherein said dielectric layer is formed of silicon nitride.